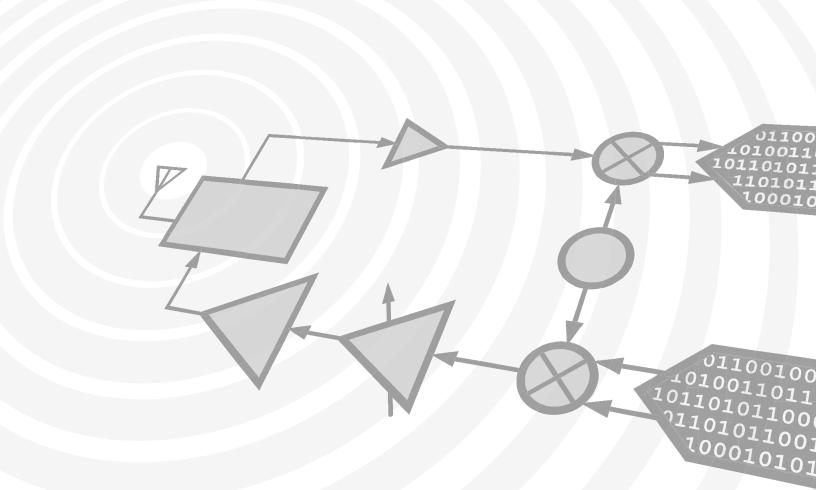




# Analog Devices Welcomes Hittite Microwave Corporation

NO CONTENT ON THE ATTACHED DOCUMENT HAS CHANGED







## GaAs MMIC MIXER w/ INTEGRATED LO AMPLIFIER, 1.2 - 2.6 GHz



#### **Typical Applications**

The HMC422MS8 / HMC422MS8E is ideal for:

- MMDS & ISM
- Wireless Local Loop
- WirelessLAN
- Cellular Infrastructure

#### **Features**

Integrated LO Amplifier w/ Pdiss <100 mW

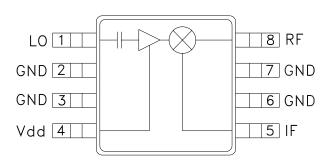
Conversion Loss / Noise Figure: 8 dB

Low LO Drive: 0 dBm

Input IP3: +15 dBm

Single Positive Supply: 3V, 30 mA

#### **Functional Diagram**



#### **General Description**

The HMC422MS8 & HMC422MS8E are double balanced mixer ICs with integrated LO amplifiers. This mixer can operate as an upconverter or downconverter between 1.2 GHz and 2.6 GHz. With the integrated LO amplifier, the mixer requires an LO drive level of only 0 dBm, and requires only 30mA from a single positive +3V rail. The mixer has 8 dB of conversion loss, an input P1dB of +8 dBm and an input third order intercept point of +15 dBm at 2 GHz.

### Electrical Specifications, $T_A = +25^{\circ}$ C

Parameter	IF = 100 MHz LO = 0 dBm & Vdd = 3V			Units
	Min.	Тур.	Max.	
Frequency Range, RF & LO 1.2 - 2.6			GHz	
Frequency Range, IF	DC - 1			GHz
Conversion Loss		8	10.5	dB
Noise Figure (SSB)		8	10.5	dB
LO to RF Isolation	23	30		dB
LO to IF Isolation	9	15 - 20		dB
RF to IF Isolation	9	15 - 20		dB
IP3 (Input)	12	15		dBm
1 dB Compression (Input)	5	8		dBm
Supply Current (Idd)		37		mA

<sup>\*</sup> Unless otherwise noted, all measurements performed as downconverter, IF= 100 MHz.

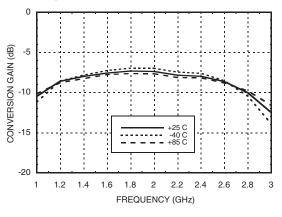




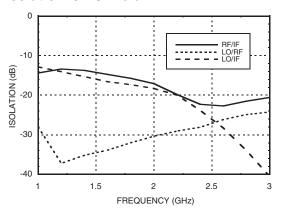
## GaAs MMIC MIXER w/ INTEGRATED LO AMPLIFIER, 1.2 - 2.6 GHz



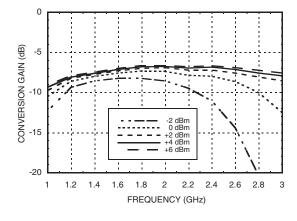
**Conversion Gain** vs. Temperature @ LO = 0 dBm



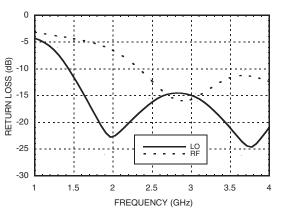
Isolation @ LO = 0 dBm



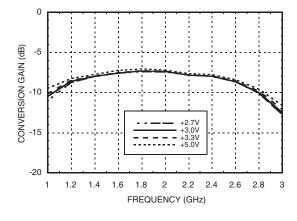
#### Conversion Gain vs. LO Drive



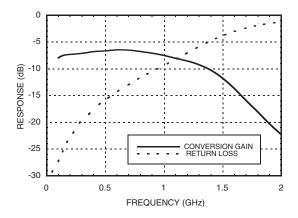
Return Loss @ LO = 0 dBm



#### **Conversion Gain** vs. Vdd @ LO = 0 dBm



IF Bandwidth @ LO = 0 dBm

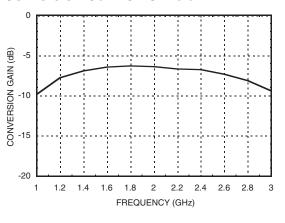




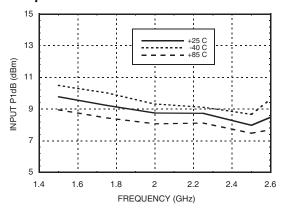
# GaAs MMIC MIXER w/ INTEGRATED LO AMPLIFIER, 1.2 - 2.6 GHz



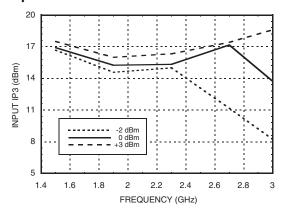
#### Upconverter Performance Conversion Gain @ LO = 0 dBm



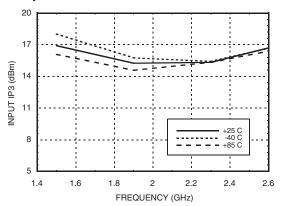
# Input P1dB vs. Temperature @ LO = 0 dBm



#### Input IP3 vs. LO Drive\*



Input IP3 vs.
Temperature @ LO = 0 dBm\*



#### **MxN Spurious @ IF Port**

	nLO				
mRF	0	1	2	3	4
0	XX	2	22	26	41
1	10	0	27	48	57
2	66	60	64	53	73
3	>85	>85	83	69	80
4	>85	>85	>85	>85	>85

RF = 2.1 GHz @ -10 dBm LO = 2 GHz @ 0 dBm

All values in dBc relative to the IF power level.

#### Harmonics of LO

	nLO Spur @ RF Port			
LO Freq. (GHz)	1	2	3	4
1.5	33	14	38	35
1.75	30	16	39	44
2	29	17	45	47
2.25	27	20	50	52
2.5	25	26	49	61
3	22	37	69	72

LO = 0 dBm

All values in dBc below input LO level @ RF port.

<sup>\*</sup> Two-tone input power= 0 dBm each tone, 1 MHz spacing.



# GaAs MMIC MIXER w/ INTEGRATED LO AMPLIFIER, 1.2 - 2.6 GHz

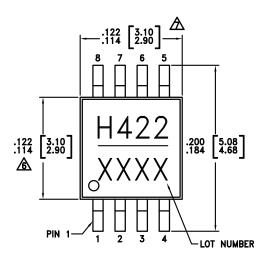


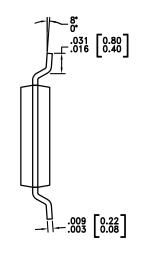
#### **Absolute Maximum Ratings**

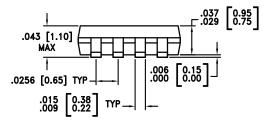
RF / IF Input (Vdd = +3V)	+13 dBm	
LO Drive (Vdd = +3V)	+13 dBm	
Vdd	+7 Vdc	
IF DC Current	±10 mA	
Channel Temperature (Tc)	150 °C	
Continuous Pdiss (T = 85°C) (Derate 5.8 mW/°C above 85 C)	0.38 W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	



#### **Outline Drawing**







- 1. PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
- 2. LEAD MATERIAL: COPPER ALLOY
- 3. LEAD PLATING: 100% MATTE TIN.
- 4. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 5. CHARACTERS TO BE HELVETICA MEDIUM, .030 HIGH, LASER OR WHITE INK, LOCATED
- APPROXIMATELY AS SHOWN.
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- 7. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- 8. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND

#### Package Information

Part Nur	mber	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC422	MS8	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H422 XXXX
HMC422N	MS8E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H422 XXXX

- [1] Max peak reflow temperature of 235 °C
- [2] Max peak reflow temperature of 260 °C
- [3] 4-Digit lot number XXXX





## GaAs MMIC MIXER w/ INTEGRATED LO AMPLIFIER, 1.2 - 2.6 GHz

#### **Pin Descriptions**

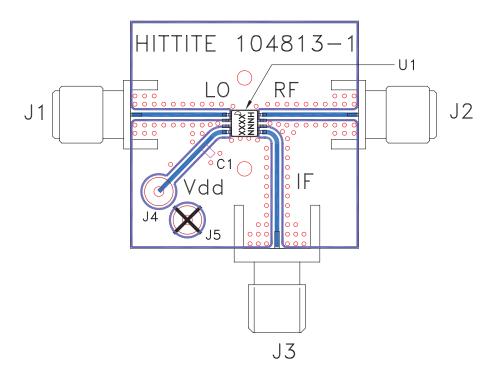
Pin Number	Function	Description	Interface Schematic
1	LO	This pin is AC coupled and matched to 50 Ohms.	LO O
2, 3, 6, 7	GND	Pins must connect to RF ground.	⊖ GND
4	Vdd	Power supply for the LO Amplifier. One external RF bypass capacitor (10,000 pF) is required.	Vdd 0———————————————————————————————————
5	IF	This pin is DC coupled. For applications not requiring operation to DC, this port should be DC blocked externally using a series capacitor whose value has been chosen to pass the necessary IF frequency range. For operation to DC, this pin must not source/sink more than 10 mA of current or die non-function and possible die failure will result.	IF O
8	RF	This pin is DC coupled and matched to 50 Ohms.	RF O





# GaAs MMIC MIXER w/ INTEGRATED LO AMPLIFIER, 1.2 - 2.6 GHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 105188 [1]

Item	Description	
J1 - J3	PCB Mount SMA RF Connector	
J4 - J5	DC Pin	
C1	10k pF Chip Capacitor, 0603 Pkg.	
U1 HMC422MS8 / HMC422MS8E Mixer		
PCB [2] 104813 Evaluation PCB, 1.0" x 1.0"		

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB  $\,$ 

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

<sup>[2]</sup> Circuit Board Material: Rogers 4350

# **Mouser Electronics**

**Authorized Distributor** 

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Analog Devices Inc.:

HMC422MS8E HMC422MS8 HMC422MS8ETR